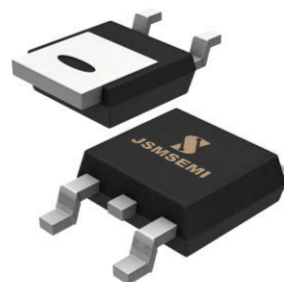


## Description:

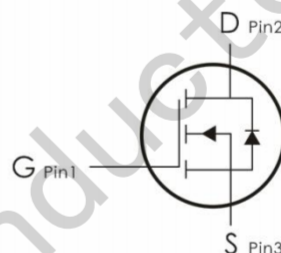
This N-Channel MOSFET uses advanced trench technology and design to provide excellent  $R_{DS(on)}$  with low gate charge.

It can be used in a wide variety of applications.



## Features:

- 1)  $V_{DS}=60V, I_D=30A, R_{DS(ON)} < 30m\Omega @ V_{GS}=10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low  $R_{DS(ON)}$ .
- 5) Excellent package for good heat dissipation.



## Absolute Maximum Ratings: ( $T_C=25^\circ C$ unless otherwise noted)

| Symbol         | Parameter                                        | Ratings     | Units         |
|----------------|--------------------------------------------------|-------------|---------------|
| $V_{DS}$       | Drain-Source Voltage                             | 60          | V             |
| $V_{GS}$       | Gate-Source Voltage                              | $\pm 20$    | V             |
| $I_D$          | Continuous Drain Current- $T_C=25^\circ C$       | 30          | A             |
|                | Continuous Drain Current- $T_C=100^\circ C$      | 16          |               |
| $I_{DM}$       | Drain Current - Pulsed1                          | 100         | A             |
| $E_{AS}$       | Single Pulse Avalanche Energy (note1)            | 24          | mJ            |
| $I_{AS}$       | Avalanche Current (note2)                        | 22          | A             |
| $P_D$          | Power Dissipation                                | 40          | W             |
|                | Power Dissipation - Derate above $25^\circ C$    | 0.32        | W/ $^\circ C$ |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range | -55 to +150 | $^\circ C$    |

**Thermal Characteristics:**

| Symbol          | Parameter                               | Max | Units                       |
|-----------------|-----------------------------------------|-----|-----------------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case    | 3.1 | $^{\circ}\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 62  |                             |

**Electrical Characteristics:** ( $T_C=25^{\circ}\text{C}$  unless otherwise noted)

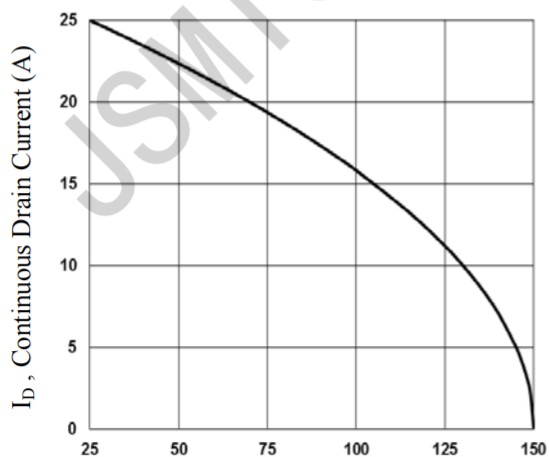
| Symbol                    | Parameter                          | Conditions                                                                  | Min | Typ  | Max   | Units |
|---------------------------|------------------------------------|-----------------------------------------------------------------------------|-----|------|-------|-------|
| Off Characteristics       |                                    |                                                                             |     |      |       |       |
| BV <sub>DSS</sub>         | Drain-Source Breakdown Voltage     | V <sub>GS</sub> =0V, I <sub>D</sub> =250 μ A                                | 60  | ---  | ---   | V     |
| ΔBVDSS/ΔT <sub>J</sub>    | BVDSS Temperature Coefficient      | Reference to 25 °C , I <sub>D</sub> =1mA                                    | --- | 0.07 | ---   | V/°C  |
| I <sub>DSS</sub>          | Zero Gate Voltage Drain Current    | V <sub>GS</sub> =0V, V <sub>DS</sub> =650V                                  | --- | ---  | 1     | μ A   |
|                           |                                    | V <sub>GS</sub> =0V, V <sub>DS</sub> =480V, T <sub>J</sub> =125 °C          | --- | ---  | 10    | μ A   |
| I <sub>GSS</sub>          | Gate-Source Leakage Current        | V <sub>GS</sub> = ± 30V, V <sub>DS</sub> =0A                                | --- | ---  | ± 100 | nA    |
| On Characteristics        |                                    |                                                                             |     |      |       |       |
| V <sub>GS(th)</sub>       | GATE-Source Threshold Voltage      | V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250 μ A                  | 1.2 | 1.7  | 2.5   | V     |
| R <sub>DS(ON)</sub>       | Drain-Source On Resistance         | V <sub>GS</sub> =10V, I <sub>D</sub> =15A                                   | --- | 25   | 30    | m Ω   |
|                           |                                    | V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A                                  | --- | 31   | 40    | m Ω   |
| Dynamic Characteristics   |                                    |                                                                             |     |      |       |       |
| C <sub>iss</sub>          | Input Capacitance                  | V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz                           | --- | 1150 | 1700  | pF    |
| C <sub>oss</sub>          | Output Capacitance                 |                                                                             | --- | 60   | 90    |       |
| C <sub>rss</sub>          | Reverse Transfer Capacitance       |                                                                             | --- | 43   | 65    |       |
| Switching Characteristics |                                    |                                                                             |     |      |       |       |
| t <sub>d(on)</sub>        | Turn-On Delay Time <sup>2,3</sup>  | V <sub>DD</sub> =30V, I <sub>D</sub> =1A,<br>R <sub>G</sub> =6 Ω (Note 3,4) | --- | 15   | 40    | ns    |
| t <sub>r</sub>            | Rise Time <sup>2,3</sup>           |                                                                             | --- | 4.5  | 8     | ns    |
| t <sub>d(off)</sub>       | Turn-Off Delay Time <sup>2,3</sup> |                                                                             | --- | 27   | 50    | ns    |

|                                    |                                           |                                                     |     |     |     |    |
|------------------------------------|-------------------------------------------|-----------------------------------------------------|-----|-----|-----|----|
| $t_f$                              | Fall Time <sup>2,3</sup>                  | $V_{GS}=30V, V_{DS}=10V,$<br>$I_D=20A$ (Note 3,4)   | --- | 7.5 | 13  | ns |
| $Q_g$                              | Total Gate Charge <sup>2,3</sup>          |                                                     | --- | 16  | 20  | nC |
| $Q_{gs}$                           | Gate-Source Charge <sup>2,3</sup>         |                                                     | --- | 2   | 4   | nC |
| $Q_{gd}$                           | Gate-Drain “Miller” Charge <sup>2,3</sup> |                                                     | --- | 3.5 | 7   | nC |
| Drain-Source Diode Characteristics |                                           |                                                     |     |     |     |    |
| $V_{SD}$                           | Diode Forward Voltage                     | $V_{GS}=0V, I_S=1A,$                                | --- | --- | 1   | V  |
| $I_S$                              | Continuous Source Current                 | ---                                                 | --- | --- | 25  | A  |
| $I_{SM}$                           | Pulsed Source Current                     | ---                                                 | --- | --- | 100 | A  |
| $T_{rr}$                           | Reverse Recovery Time                     | $V_{GS}=0V, I_S=1A,$<br>$dI/dt=100A/\mu s$ (Note 3) | --- | 17  | --- | ns |
| $Q_{rr}$                           | Reverse Recovery Charge                   |                                                     | --- | 12  | --- | nC |

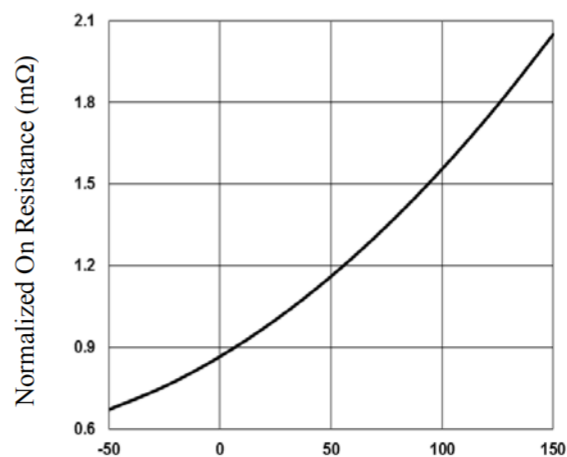
### Notes:

- 1.Repetitive Rating : Pulsed width limited by maximum junction temperature.
- 2.VDD=25V,VGS=10V,L=0.1mH,IAS=22A.,RG=25 ,Starting TJ=25℃
- 3.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$ .
- 4.Essentially independent of operating temperature.

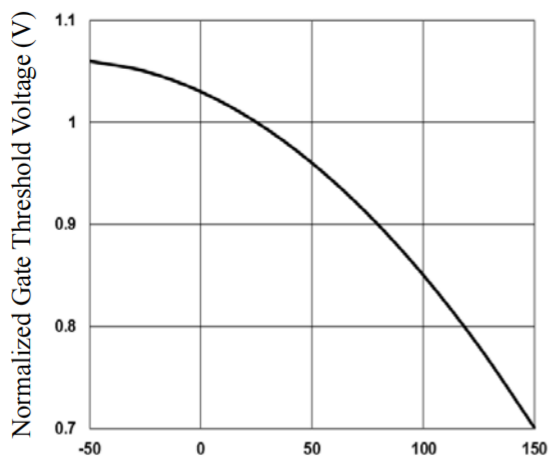
### Typical Characteristics: (T<sub>c</sub>=25℃ unless otherwise noted)



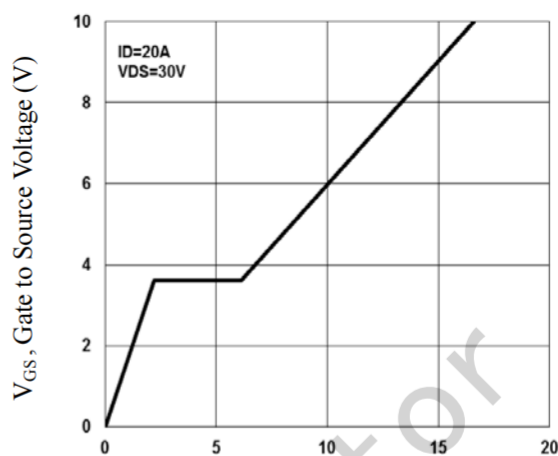
**Fig.1 Continuous Drain Current vs. T<sub>c</sub>**



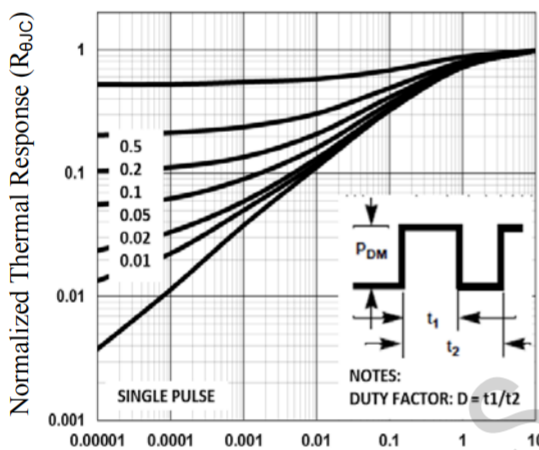
**Fig.2 Normalized R<sub>DS(on)</sub> vs. T<sub>j</sub>**



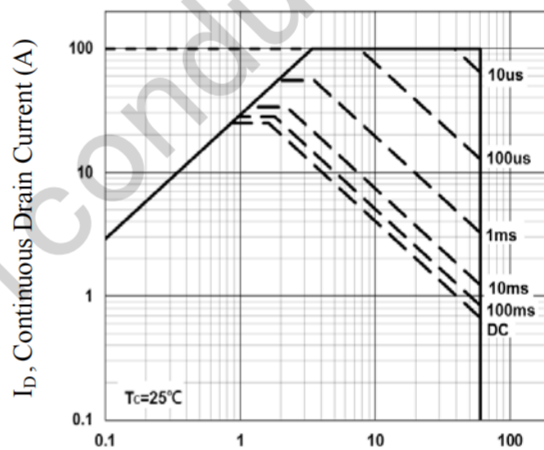
**Fig.3 Normalized  $V_{th}$  vs.  $T_j$**



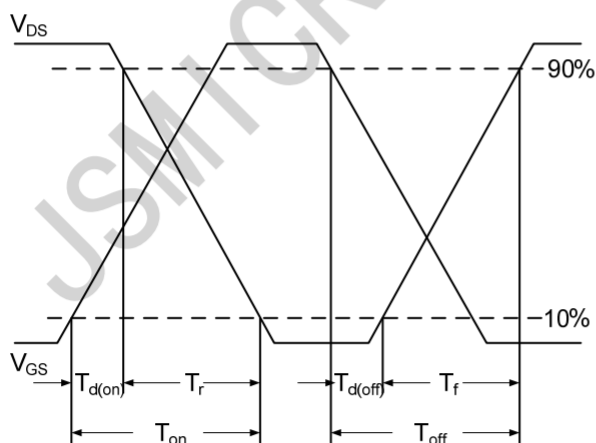
**Fig.4 Gate Charge Waveform**



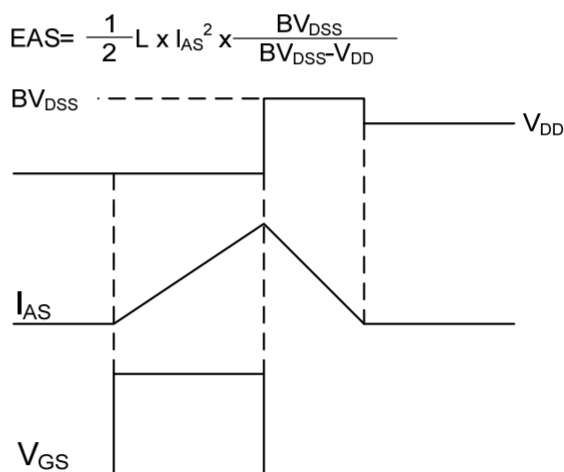
**Fig.5 Normalized Transient Impedance**



**Fig.6 Maximum Safe Operation Area**



**Fig.7 Switching Time Waveform**

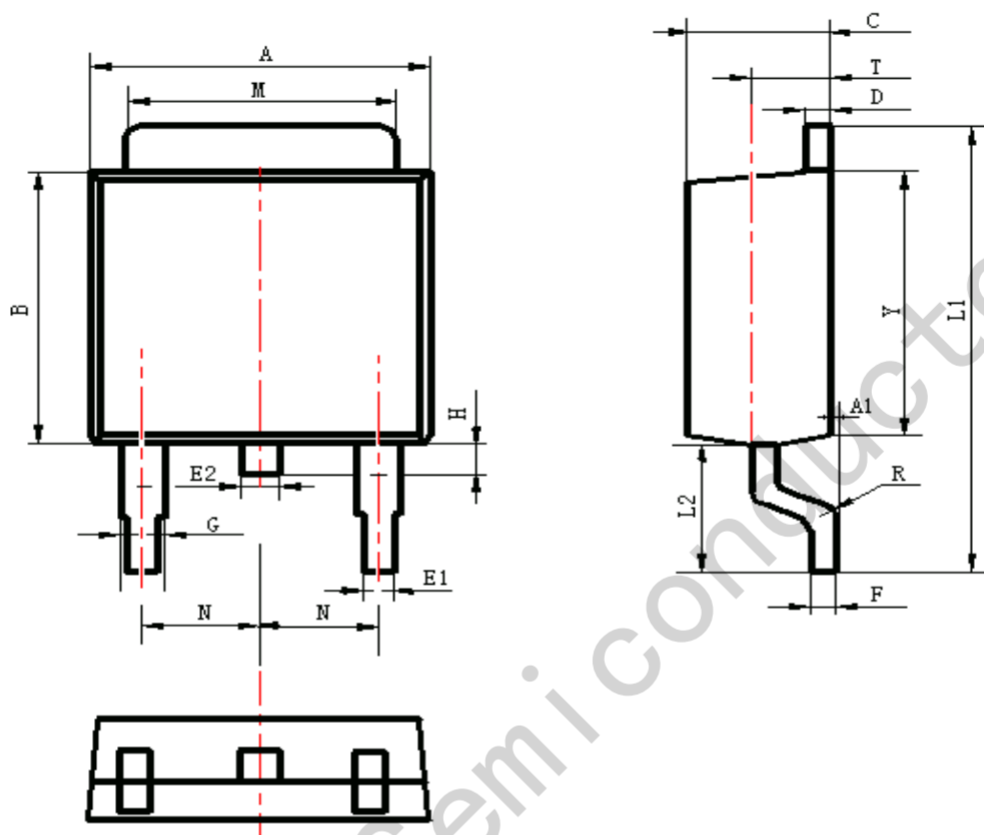


**Fig.8 EAS Waveform**

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

## Package Information

TO-252



| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |
|--------|---------------------------|-------|----------------------|-------|
|        | Min.                      | Max.  | Min.                 | Max.  |
| A      | 6.30                      | 6.90  | 0.248                | 0.272 |
| A1     | 0.00                      | 0.16  | 0.000                | 0.006 |
| B      | 5.70                      | 6.30  | 0.224                | 0.248 |
| C      | 2.10                      | 2.50  | 0.083                | 0.098 |
| D      | 0.30                      | 0.70  | 0.012                | 0.028 |
| E1     | 0.60                      | 0.90  | 0.024                | 0.035 |
| E2     | 0.70                      | 1.00  | 0.028                | 0.039 |
| F      | 0.30                      | 0.60  | 0.012                | 0.024 |
| G      | 0.70                      | 1.20  | 0.028                | 0.047 |
| L1     | 9.60                      | 10.50 | 0.378                | 0.413 |
| L2     | 2.70                      | 3.10  | 0.106                | 0.122 |
| H      | 0.40                      | 1.00  | 0.016                | 0.039 |
| M      | 5.10                      | 5.50  | 0.201                | 0.217 |
| N      | 2.09                      | 2.49  | 0.082                | 0.098 |
| R      | 0.30                      |       | 0.012                |       |
| T      | 1.40                      | 1.60  | 0.055                | 0.063 |
| Y      | 5.10                      | 6.30  | 0.201                | 0.248 |